# NPN General - Purpose Amplifier

# 2N3904

#### **Description**

This device is designed as a general-purpose amplifier and switch. The useful dynamic range extends to 100 mA as a switch and to 100 MHz as an amplifier.

#### **MAXIMUM RATINGS**

(Values are at  $T_A = 25^{\circ}C$  unless otherwise noted.) (Note 1, Note 2)

Symbol	nbol Parameter		Unit	
V <sub>CEO</sub>	Collector - Emitter Voltage	40	V	
V <sub>CBO</sub>	Collector - Base Voltage	60	٧	
V <sub>EBO</sub>	Emitter – Base Voltage	6.0	V	
Ic	Collector Current - Continuous	200	mA	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. These ratings are based on a maximum junction temperature of 150°C.
- These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed orlow-duty cycle operations.

#### THERMAL CHARACTERISTICS

(Values are at T<sub>A</sub> = 25°C unless otherwise noted.)

Symbol	Parameter	Max	Unit
$P_{D}$	Total Device Dissipation	625	mW
	Derate Above 25°C	5.0	mW/°C
$R_{ hetaJC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient	200	°C/W



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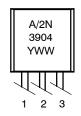




TO-92 3 CASE 135AN

TO-92 3 LEADFORMED CASE 135AR

#### **MARKING DIAGRAM**



- 1: Emitter
- 2: Base
- 3: Collector

A = Assembly Code 2N3904 = Device Code YWW = Date Code

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

#### 2N3904

# **ELECTRICAL CHARACTERISTICS** (Values are at $T_A$ = 25°C unless otherwise noted.)

Symbol	Parametr	Conditions	Min	Max	Unit
FF CHARACTER	RISTICS	•	•	•	
V <sub>(BR)CEO</sub>	Collector - Emitter Breakdown Voltage	$I_C = 1.0 \text{ mA}, I_B = 0$	40	-	V
V <sub>(BR)CBO</sub>	Collector - Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	60	-	V
V <sub>(BR)EBO</sub>	Emitter – Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	6.0	-	V
I <sub>BL</sub>	Base Cutoff Current	V <sub>CE</sub> = 30 V, V <sub>EB</sub> = 3 V	-	50	nA
I <sub>CEX</sub>	Collector Cut-Off Current	V <sub>CE</sub> = 30 V, V <sub>EB</sub> = 3 V	-	50	nA
N CHARACTERI	STICS (Note 3)				
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 0.1 mA, V <sub>CE</sub> = 1.0 V	40	-	_
		I <sub>C</sub> = 1.0 mA, V <sub>CE</sub> = 1.0 V	70	-	1
		I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 1.0 V	100	300	
		$I_C = 50 \text{ mA}, V_{CE} = 1.0 \text{ V}$	60	-	
		I <sub>C</sub> = 100 mA, V <sub>CE</sub> = 1.0 V	30	-	
V <sub>CE(sat)</sub>	Collector - Emitter Saturation Voltage	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 1.0 mA	-	0.2	V
		$I_C = 50.0 \text{ mA}, I_B = 5.0 \text{ mA}$	- 0.3	1	
V <sub>BE(sat)</sub>	Base - Emitter Saturation Voltage	I <sub>C</sub> = 10.0 mA, I <sub>B</sub> = 1.0 mA	0.65	0.85	V
		$I_C = 50.0 \text{ mA}, I_B = 5.0 \text{ mA}$	-	0.95	1
MALL-SIGNAL	CHARACTERISTICS	•	•	•	•
f <sub>T</sub>	Current - Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 20 \text{ V},$ f = 100 MHz	300	_	MHz
$C_{obo}$	Output Capacitance	V <sub>CB</sub> = 5.0 V, I <sub>E</sub> = 0, f = 100 kHz	_	4.0	pF
C <sub>ibo</sub>	Input Capacitance	V <sub>EB</sub> = 0.5 V, I <sub>C</sub> = 0, f = 100 kHz	_	8.0	pF
NF	Noise Figure	$I_C$ = 100 μA, $V_{CE}$ = 5.0 V, $R_S$ = 1.0 kΩ, f = 10 Hz to 15.7 kHz	-	5.0	dB
WITCHING CHA	RACTERISTICS	•		-	-
t <sub>d</sub>	Delay Time	$V_{CC} = 3.0 \text{ V}, V_{BE} = 0.5 \text{ V},$	-	35	ns
t <sub>r</sub>	Rise Time	I <sub>C</sub> = 10 mA, I <sub>B1</sub> = 1.0 mA	-	35	ns
t <sub>s</sub>	Storage Time	$V_{CC} = 3.0 \text{ V}, I_{C} = 10 \text{ mA},$	-	200	ns
t <sub>f</sub>	Fall Time	$I_{B1} = I_{B2} = 1.0 \text{ mA}$	_	50	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2%.

#### 2N3904

#### TYPICAL PERFORMANCE CHARACTERISTICS

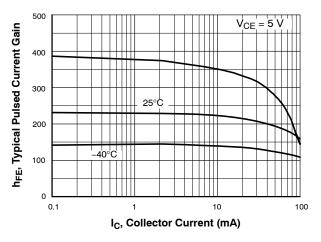


Figure 1. Typical Pulsed Current Gain vs. Collector Current

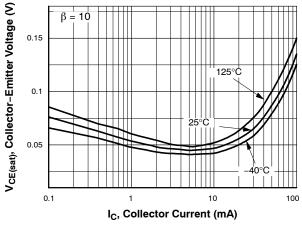


Figure 2. Collector-Emitter Saturation Voltage vs. Collector Current

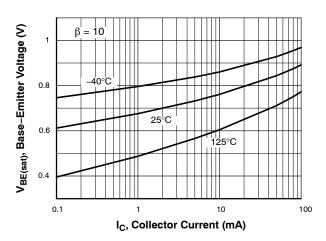


Figure 3. Base-Emitter Saturation Voltage vs. Collector Current

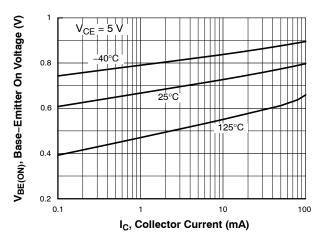


Figure 4. Base-Emitter On Voltage vs. Collector Current

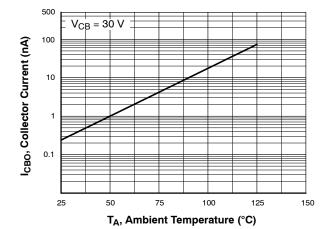


Figure 5. Collector Cut-Off Current vs. Ambient Temperature

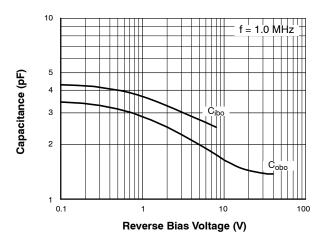


Figure 6. Capacitance vs. Reverse Bias Voltage

# TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

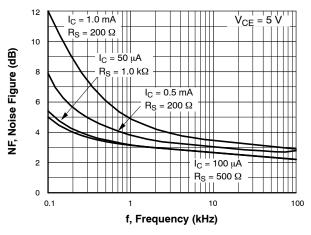


Figure 7. Noise Figure vs. Frequency

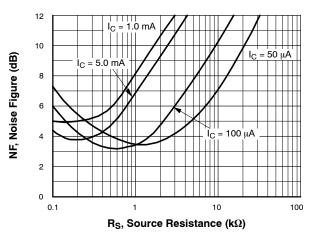


Figure 8. Noise Figure vs. Source Resistance

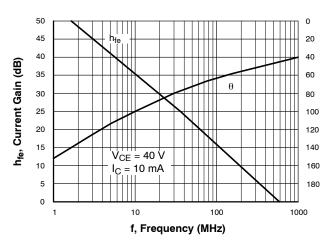


Figure 9. Current Gain and Phase Angle vs. Frequency

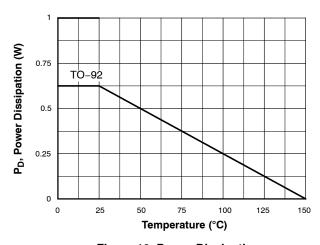


Figure 10. Power Dissipation vs. Ambient Temperature

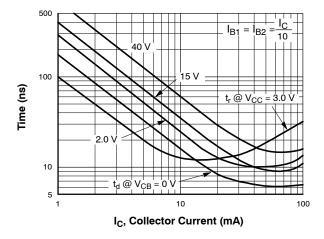


Figure 11. Turn-On Time vs. Collector Current

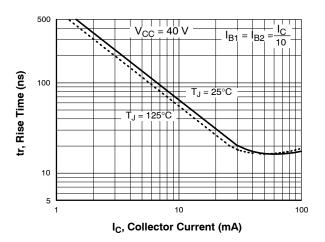


Figure 12. Rise Time vs. Collector Current

# TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

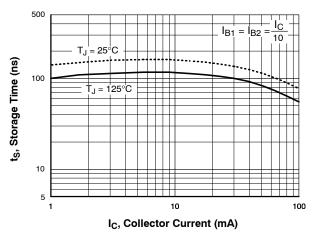


Figure 13. Storage Time vs. Collector Current

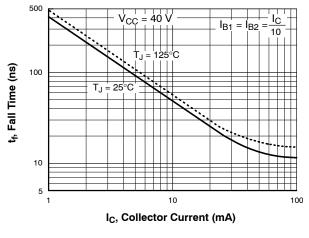


Figure 14. Fall Time vs. Collector Current

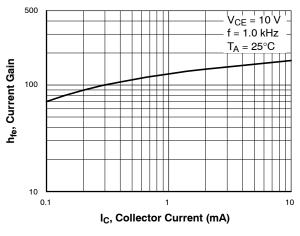


Figure 15. Current Gain

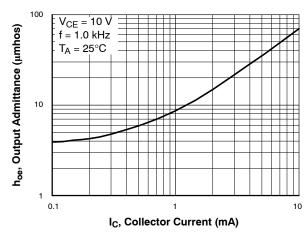


Figure 16. Output Admittance

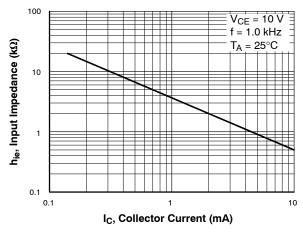


Figure 17. Input Impedance

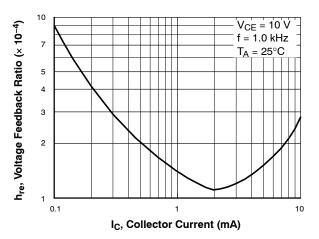


Figure 18. Voltage Feedback Ratio

#### 2N3904

# **TEST CIRCUITS**

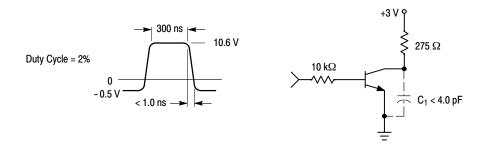


Figure 19. Delay and Rise Time Equivalent Test Circuit

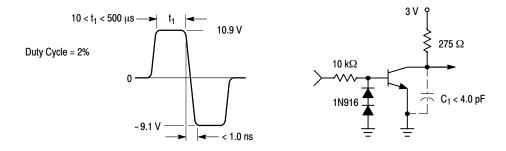


Figure 20. Storage and Fall Time Equivalent Test Circuit

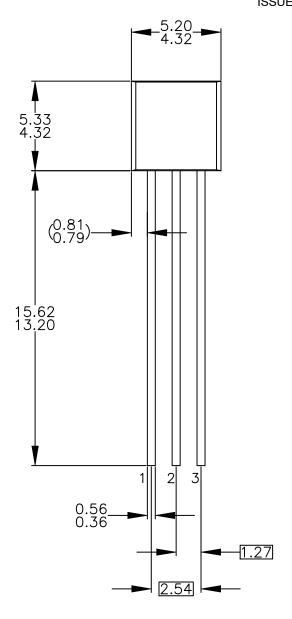
#### **ORDERING INFORMATION**

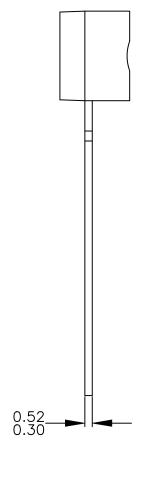
Device	Package	Shipping <sup>†</sup>
2N3904BU	TO-92-3 LF (Pb-Free)	10000 Units / Bulk Bag
2N3904TA	TO-92-3 LF (Pb-Free)	2000 Units / Fan-Fold
2N3904TAR	TO-92-3 LF (Pb-Free)	2000 Units / Fan-Fold
2N3904TF	TO-92-3 LF (Pb-Free)	2000 Units / Tape & Reel
2N3904TFR	TO-92-3 LF (Pb-Free)	2000 Units / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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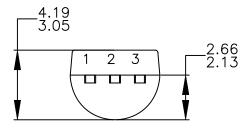
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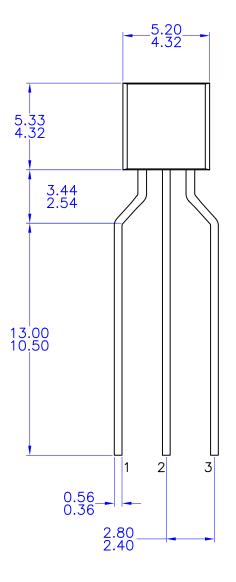
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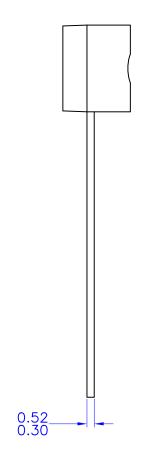
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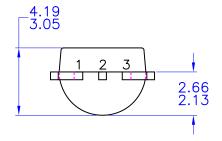
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